

40V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
40V	9.5mΩ @ V _{GS} = 10V	11.8A
400	15.5mΩ @ V _{GS} = 4.5V	9.2A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

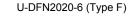
- **Power Management Functions**
- **DC-DC Converters**
- Backlighting

Features

- Low R_{DS(ON)} Ensures on state losses are minimized
- Excellent $Q_{gd} \times R_{DS(ON)}$ Product (FOM)
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

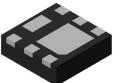
Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4
- Weight: 0.0065 grams (Approximate)

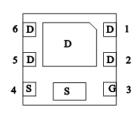




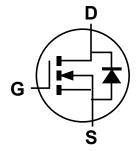
Top View



Bottom View



Pin Out **Bottom View**



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Quantity per Reel
DMT4008LFDF-7	U-DFN2020-6 (Type F)	3000
DMT4008LFDF-13	U-DFN2020-6 (Type F)	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1:



8M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H= 2020) M = Month (ex: 9 = September)

Date Code Key

	Year	2013	 2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Ī	Code	Α	 G	Н	I	J	K	L	M	N	0	Р

Ī	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Ī	Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2:



A-Z

8M = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: H = 2020) W = Week (ex: a = week 27; z represents week 52 and 53) X = Internal code (ex: U = Monday)

Date Code Key

Code

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	0	1	2	3	4	5	6	7	8
Week	Week 1-26			27-52			53		

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Codo	Т	- 11	V	W	V	V	7

DMT4008LFDF
Datasheet number: DS39333 Rev. 4 - 2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	11.8 9.4	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	70	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	70	Α
Continuous Source-Drain Diode Current	I _S	2.2	Α	
Avalanche Current, L = 0.3mH	I _{AS}	13.3	Α	
Avalanche Energy, L = 0.3mH		Eas	26.5	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	8.0	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	155	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P_{D}	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)		R _{0JA}	63	°C/W
Thermal Resistance, Junction to Case (Note 6)	T _C = +25°C	$R_{ heta JC}$	8.9	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

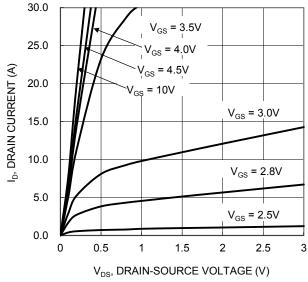
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

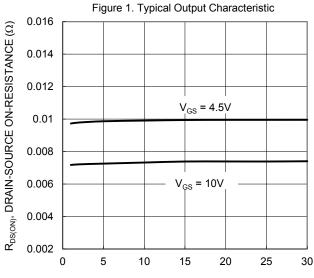
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current (T _J = +25°C)	I _{DSS}	_	_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	1.7	3	>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	7.8	9.5	mΩ	$V_{GS} = 10V, I_D = 10A$	
Static Drain-Source On-Resistance	KDS(ON)	_	10.6	15.5	11122	$V_{GS} = 4.5V, I_D = 8.5A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 10A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	1179	_		V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	384	-	pF		
Reverse Transfer Capacitance	C _{rss}	_	42	_			
Gate Resistance	R_{G}	_	1.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_G	_	8.3	_			
Total Gate Charge (V _{GS} = 10V)	Q_G	_	17.1	_	nC	V _{DD} = 20V. I _D = 10A	
Gate-Source Charge	Q_{GS}	_	2.4	_	IIC	V _{DD} = 20V, I _D = 10A	
Gate-Drain Charge	Q_{GD}	_	3.4	_			
Turn-On Delay Time	t _{D(ON)}	_	3.5	_			
Turn-On Rise Time	t _R	_	3.7	_		$V_{DD} = 20V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	17.1	_	ns	$R_G = 6\Omega$, $I_D = 10A$	
Turn-Off Fall Time	t _F	_	6.4	_			
Reverse Recovery Time	t _{RR}	_	19.8	_	ns	1 - 404 4:/44 - 4004/	
Reverse Recovery Charge	Q_{RR}	_	8.8	_	nC	$I_F = 10A$, di/dt = 100A/ μ s	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect. Notes:

8. Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

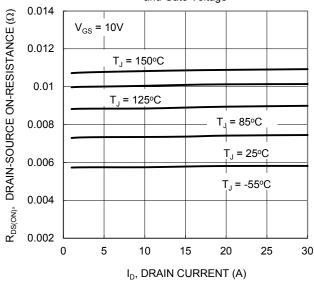


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

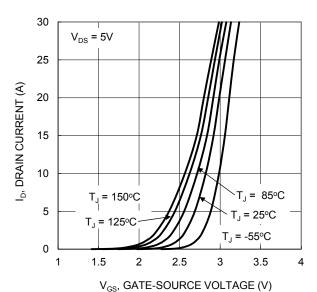


Figure 2. Typical Transfer Characteristic

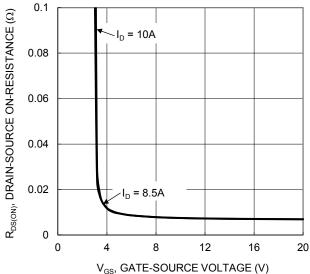


Figure 4. Typical Transfer Characteristic

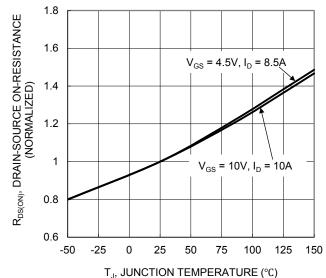


Figure 6.On-Resistance Variation with Junction Temperature



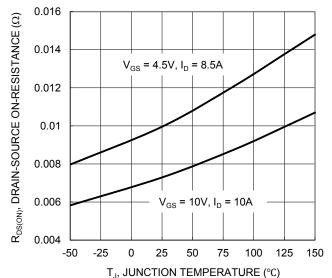
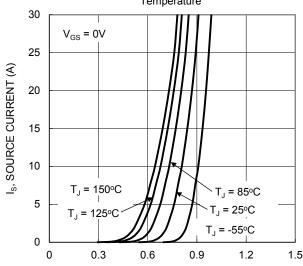


Figure 7. On-Resistance Variation with Junction Temperature



 $\rm V_{SD},$ SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

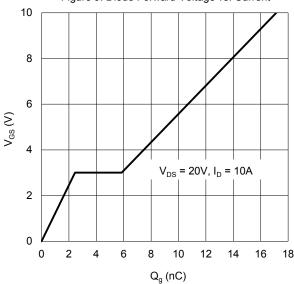


Figure 11. Gate Charge

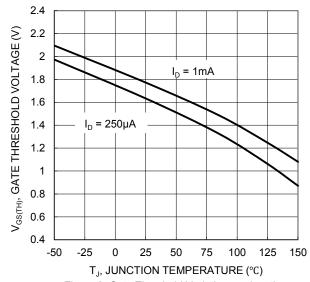
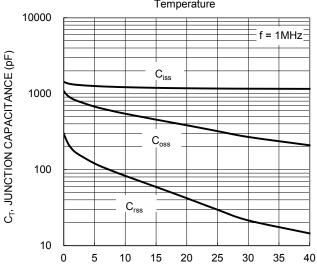


Figure 8. Gate Threshold Variation vs. Junction Temperature



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance

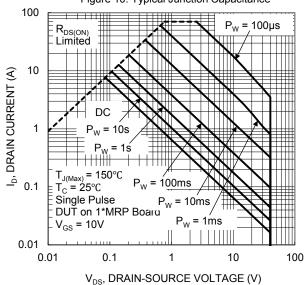


Figure 12. SOA, Safe Operation Area

March 2020

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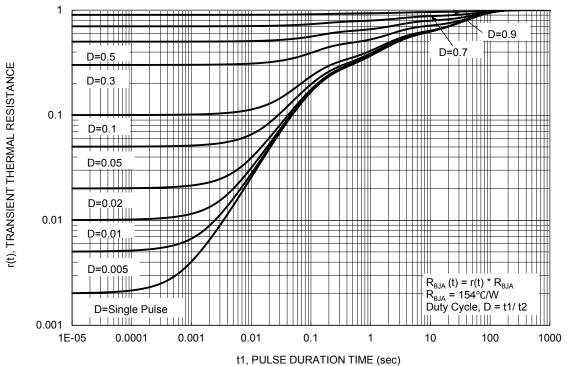


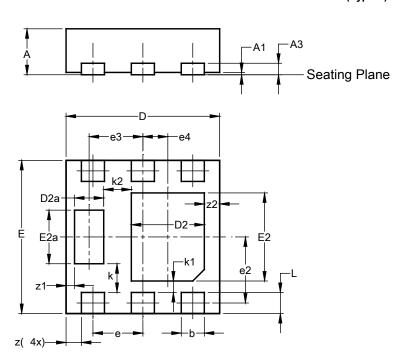
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

U-DFN2020-6 (Type F)

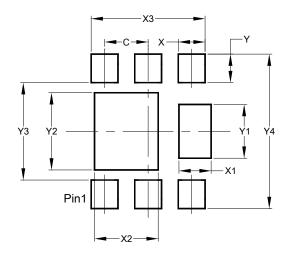


	U-DFN2020-6							
	(Тур	oe F)						
Dim	Min	Max	Тур					
Α	0.57	0.57 0.63 0.60						
A1	0.00	0.00 0.05 0.03						
A3	-	-	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.43	0.38					
Е	1.95 2.05 2.00							
E2	1.05 1.25 1.15							
E2a	0.65 0.75 0.70							
е		0.65 BS	С					
e2	().863 BS	SC					
е3		0.70 BS	С					
e4	().325 BS	SC					
k		0.37 BS	С					
k1		0.15 BS	С					
k2	0.36 BSC							
L	0.225 0.325 0.275							
Z	0.20 BSC							
z1	0.110 BSC							
z2		0.20 BSC						
All C	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value
Dillielisions	(in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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